



RSD201N10TL Information



For Reference Only

Part Number RSD201N10TL Manufacturer Rohm Semiconductor

Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single

MOSFET N-CH 100V 20A CPT3

Description TO-252-3, DPak (2 Leads + Tab), SC-63

Package For the pricing/inventory/lead time, please contact

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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RSD201N10TL Specifications

Manufacturer Part NumberRSD201N10TLManufacturerRohm SemiconductorCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-252-3, DPak (2 Leads + Tab), SC-63Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C20A (Tc)Drive Voltage (Max Rds On, Min Rds On)4V, 10VVgs(th) (Max) @ Id2.5V @ ImAGate Charge (Qg) (Max) @ Vgs55nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2100pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)850mW (Ta), 20W (Tc)Rds On (Max) @ Id, Vgs46 mOhm @ 20A, 10VOperating Temperature150°C (TJ)Maunting TypeSurface Mount		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 20A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4V, 10V Vgs(th) (Max) @ Id 2.5V @ ImA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 2100pF @ 25V Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 46 mOhm @ 20A, 10V Operating Temperature	Manufacturer Part Number	RSD201N10TL
Package To-252-3, DPak (2 Leads + Tab), SC-63 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 20A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4V, 10V Vgs(th) (Max) @ Id 2.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 55nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2100pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 850mW (Ta), 20W (Tc) Rds On (Max) @ Id, Vgs 46 mOhm @ 20A, 10V Operating Temperature 150°C (TJ)	Manufacturer	Rohm Semiconductor
Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series	Category	Discrete Semiconductor Products
Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 20A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4V, 10V Vgs(th) (Max) @ Id 2.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 55nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2100pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 850mW (Ta), 20W (Tc) Rds On (Max) @ Id, Vgs 46 mOhm @ 20A, 10V Operating Temperature 150°C (TJ)		Transistors - FETs, MOSFETs - Single
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Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 20A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) **ET Feature** Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature 150°C (TJ)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 20A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4V, 10V Vgs(th) (Max) @ Id 2.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 55nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2100pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 850mW (Ta), 20W (Tc) Rds On (Max) @ Id, Vgs 46 mOhm @ 20A, 10V Operating Temperature 150°C (TJ)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 2.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 55nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2100pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 850mW (Ta), 20W (Tc) Rds On (Max) @ Id, Vgs 46 mOhm @ 20A, 10V Operating Temperature	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id 2.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 55nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2100pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 850mW (Ta), 20W (Tc) Rds On (Max) @ Id, Vgs 46 mOhm @ 20A, 10V Operating Temperature 150°C (TJ)	Current - Continuous Drain (Id) @ 25°C	20A (Tc)
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Input Capacitance (Ciss) (Max) @ Vds 2100pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 850mW (Ta), 20W (Tc) Rds On (Max) @ Id, Vgs 46 mOhm @ 20A, 10V Operating Temperature 150°C (TJ)	Vgs(th) (Max) @ Id	2.5V @ 1mA
Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 850mW (Ta), 20W (Tc) Rds On (Max) @ Id, Vgs 46 mOhm @ 20A, 10V Operating Temperature 150°C (TJ)	Gate Charge (Qg) (Max) @ Vgs	55nC @ 10V
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Power Dissipation (Max) Rds On (Max) @ Id, Vgs 46 mOhm @ 20A, 10V Operating Temperature 150°C (TJ)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 46 mOhm @ 20A, 10V Operating Temperature 150°C (TJ)	FET Feature	-
Operating Temperature 150°C (TJ)	Power Dissipation (Max)	850mW (Ta), 20W (Tc)
	Rds On (Max) @ Id, Vgs	46 mOhm @ 20A, 10V
Mounting Type Surface Mount	Operating Temperature	150°C (TJ)
Widuling Type Surface Widuli	Mounting Type	Surface Mount
Supplier Device Package CPT3	Supplier Device Package	CPT3
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
Report errors?		Report errors?

RSD201N10TL Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

RSD201N10TL Payment Methods



















RSD201N10TL Shipping Methods













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